

The effect of underfill on thermal stresses on logic ASIC and its electrical performance

Babak Talebanpour, Doug Link

03/09/2017

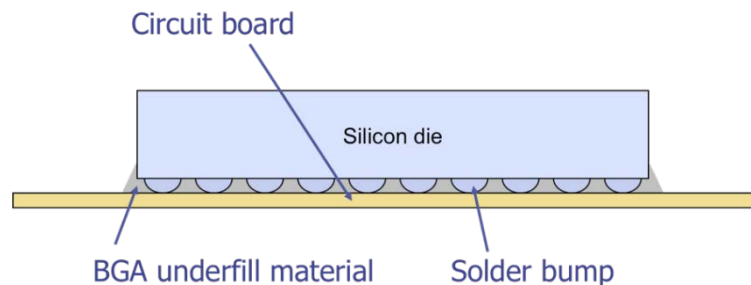


Outlines

- Introduction
 - Thermo-mechanical stresses on logic ASIC and its effects
- Finite element analysis of stresses
- Experimental observations
- Summary



Thermo-mechanical stresses on flip chip assembly



Component	Material	CTE ppm/oC
Die	Si	2.6
Micro bumps	Sn-3%Ag-0.5%Cu	21.6
Underfill	UF1	41-120
Flex PCB	Polyimide	35

Effect of Thermo-mechanical stresses on logic ASIC



Observations:

- Nominal clock for an Starkey logic die is set at 10.24 MHz
- Maximum allowable clock shift ± 0.25 %
- FC on flex circuits consistently show clock shift of above 1%, when exposed to heat events (solder reflow).
- 1 week wait from fabrication to clock calibration reduces the shift significantly.

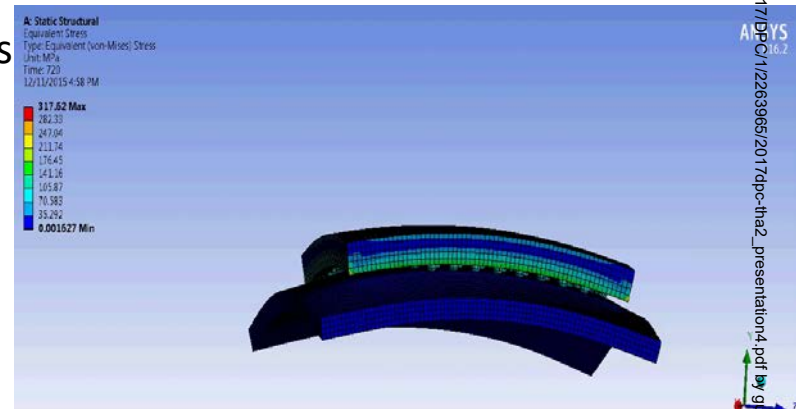
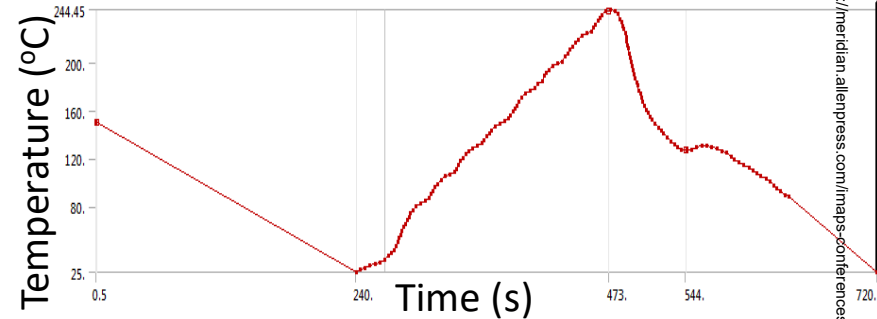
Goals:

- The cause(s) of clock shift,
- Minimize the clock shift.
 - Quick solutions.
 - Permanent solution for next gen products.

FE analysis

- Assumptions:

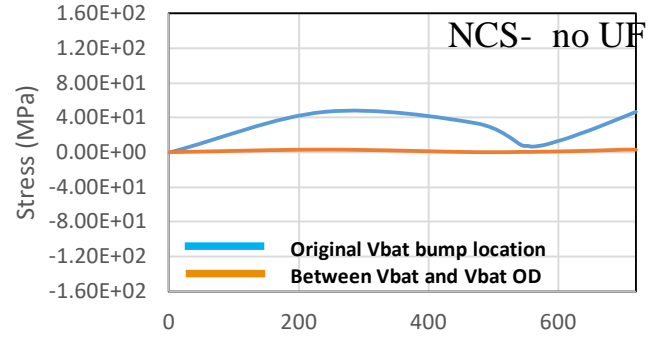
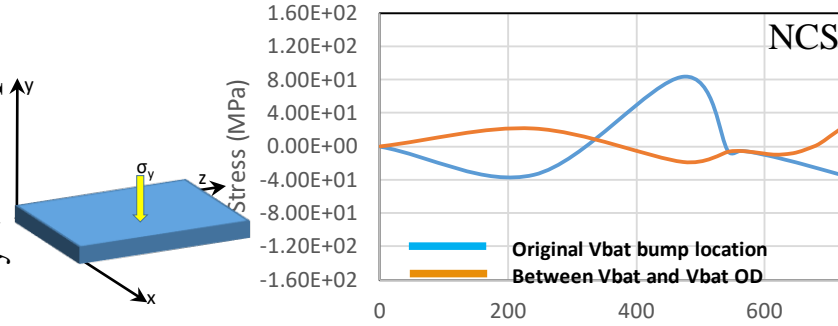
1. Perfect bonding for all contact surfaces,
2. The assembly is stress free at 150 °C (UF cure temperature),
3. No temperature gradient between components.
4. FE analysis/real life experiments on flip chip assemblies have shown the most important component of stress that adversely affects the clock is the normal (y) component.





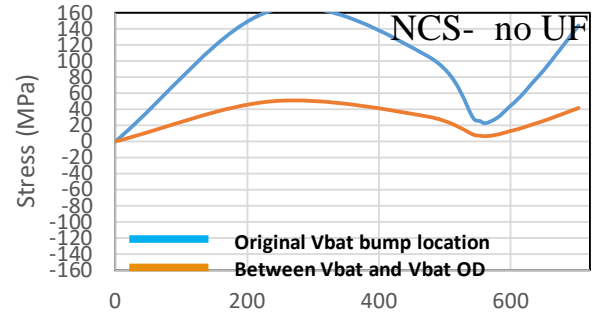
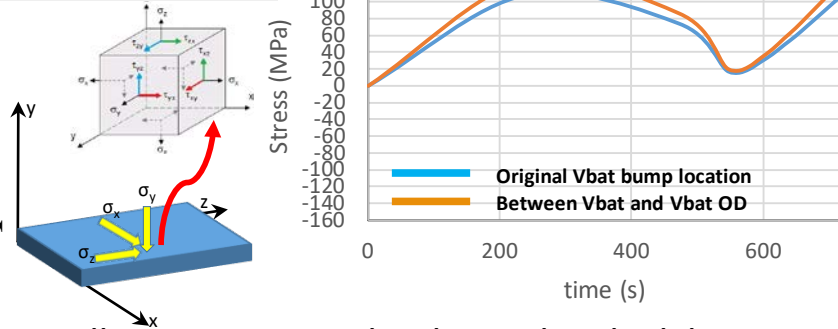
Effect of no underfill

σ_y (out of plane)



$$\sigma_{\text{vdr}} = \sqrt{0.5[(\sigma_x - \sigma_y)^2 + (\sigma_y - \sigma_z)^2 + (\sigma_z - \sigma_x)^2] + 3(\sigma_{xy}^2 + \sigma_{yz}^2 + \sigma_{zx}^2)}$$

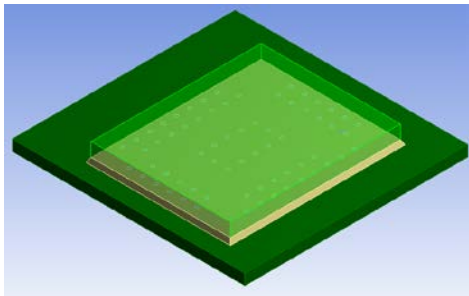
Equivalent



- smaller stresses on the die at the clock location, when UF is eliminated.
- UF reduces equivalent stress on the die, due to providing support against lateral loads on bump.

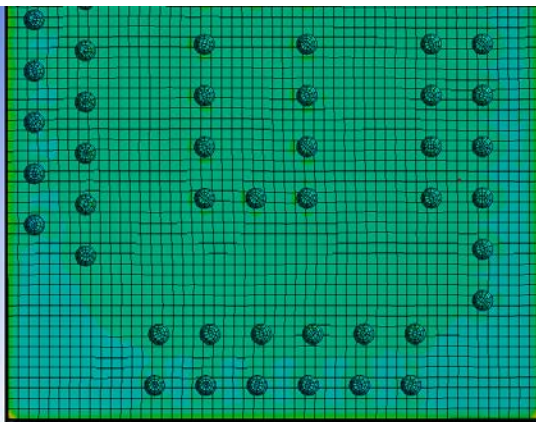
Evaluating the effect of voids

Underfill covers the whole die active layer side



A: Static Structural
Equivalent Stress
Type: Equivalent (von-Mises) Stress
Unit: MPa
Time: 720
2/8/2016 1:30 PM

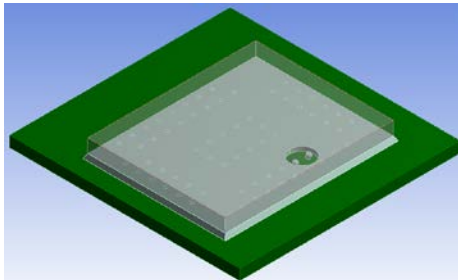
317.62 Max
291.13
264.68
238.21
211.74
185.28
158.81
132.34
105.87
79.405
52.937
26.47
0.001627 Min



0.000 0.500 1.000 (mm)
0.250 0.750

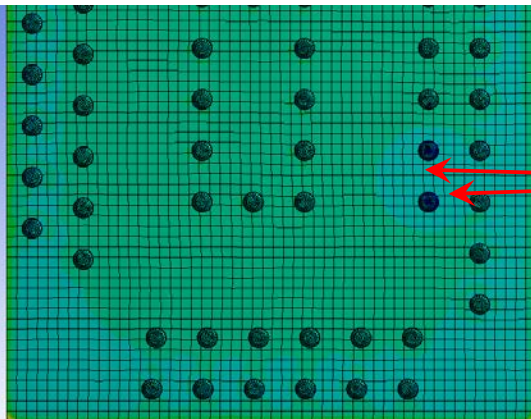
ANSYS
R16.2

UF with a void 450 microns in diameter around Vbat and Vbat O/D bumps.



A: Static Structural
Equivalent Stress
Type: Equivalent (von-Mises) Stress
Unit: MPa
Time: 702.4
2/8/2016 1:26 PM

284.19 Max
260.51
236.82
213.14
189.46
165.78
142.09
118.41
94.73
71.048
47.396
23.684
0.0014208 Min



0 (mm)

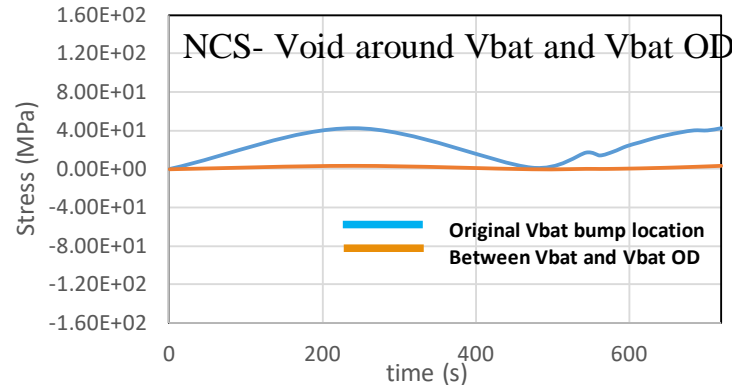
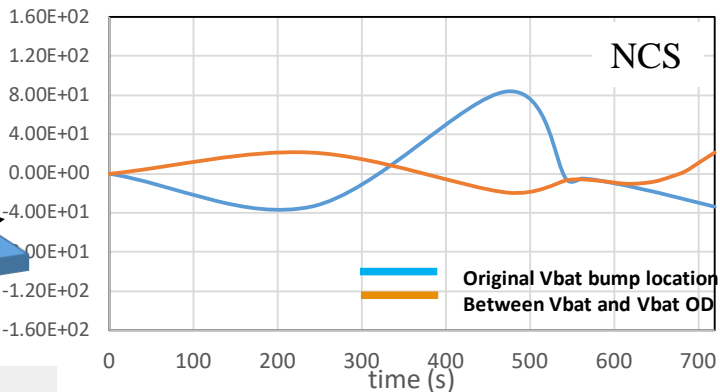
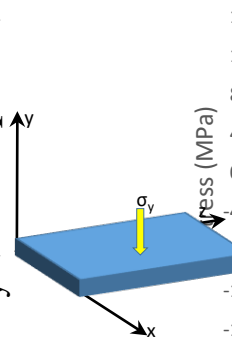
ANSYS
R16.2

Much lower stress levels on V bat and V bat O/D as well as the surrounding area.



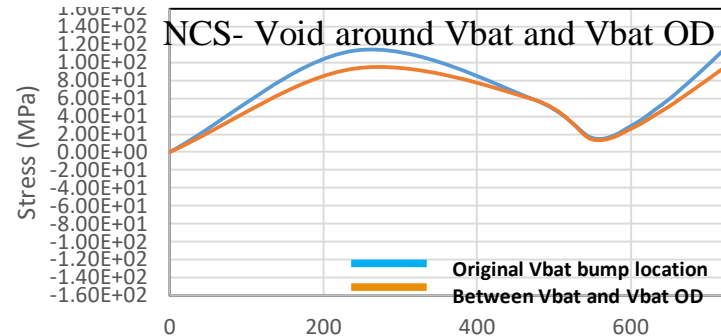
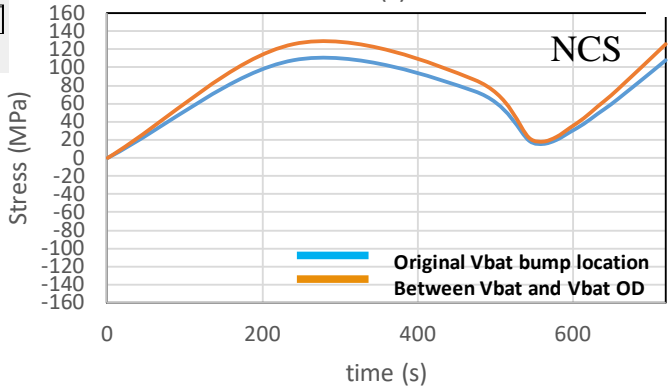
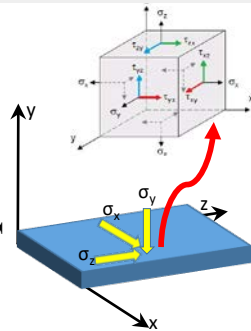
Effect of UF void on stress

σ_y (out of plane)



$$\sigma_{\text{vdr}} = \sqrt{0.5[(\sigma_x - \sigma_y)^2 + (\sigma_y - \sigma_z)^2 + (\sigma_z - \sigma_x)^2] + 3(\sigma_{xy}^2 + \sigma_{yz}^2 + \sigma_{zx}^2)}$$

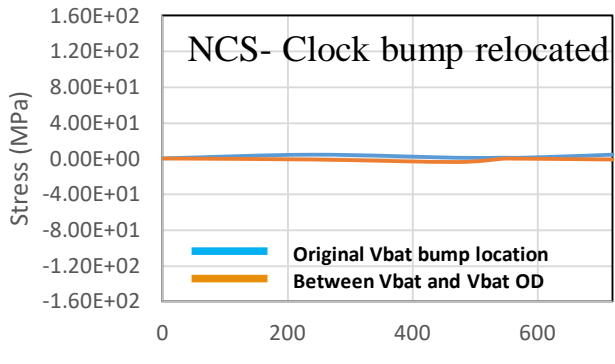
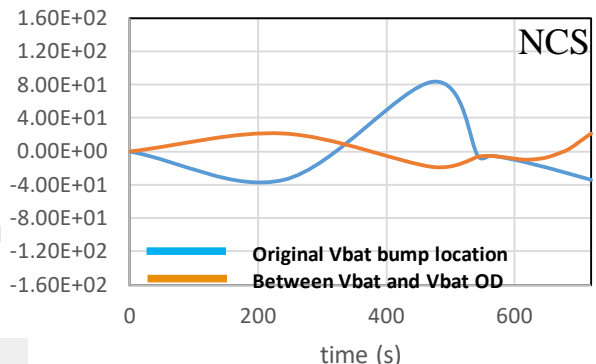
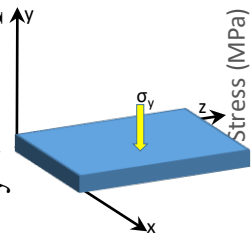
Equivalent



- much smaller stresses on the die at the original Vbat bump location or half way between Vbat and Vbat OD, when void exists around the clock circuit.
- Equivalent stresses are comparable.

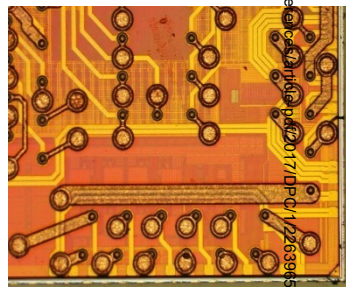
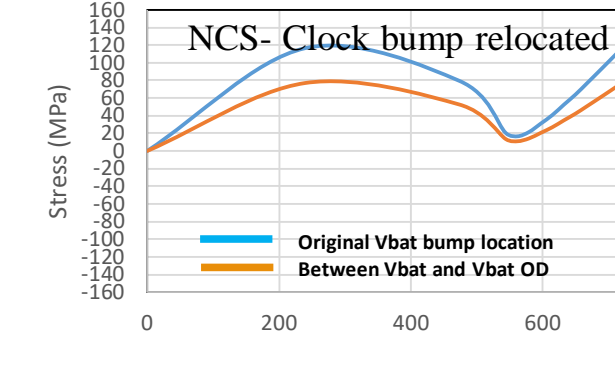
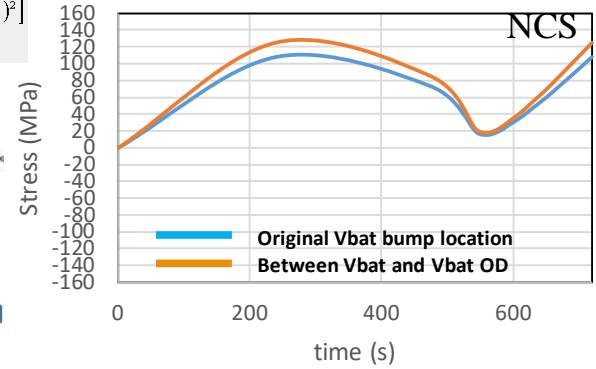
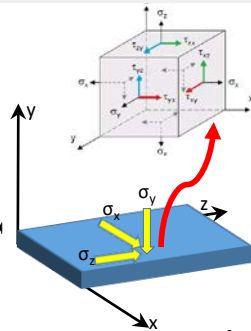
Effect of relocation of bumps

σ_y (out of plane)



$$\sigma_{\text{vbat}} = \sqrt{0.5[(\sigma_x - \sigma_y)^2 + (\sigma_y - \sigma_z)^2 + (\sigma_z - \sigma_x)^2] + 3(\sigma_{xy}^2 + \sigma_{yz}^2 + \sigma_{zx}^2)}$$

Equivalent

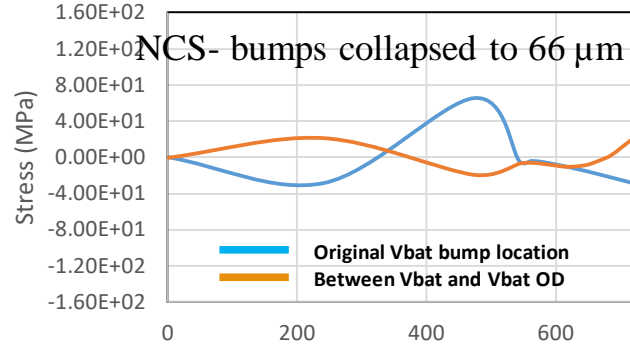
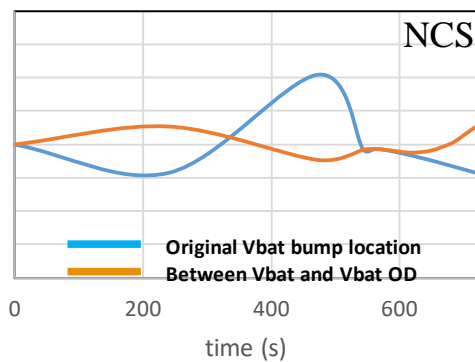
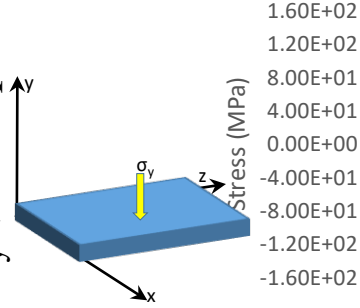


- Stress is probed at the original V bat location as well half way between Vbat and Vbat OD. Smaller stresses at both locations when Vbat is relocated according to NP5-S layout.
- Comparable values of equivalent stress.

Effect of collapsing the bumps from 80 to 66 μm

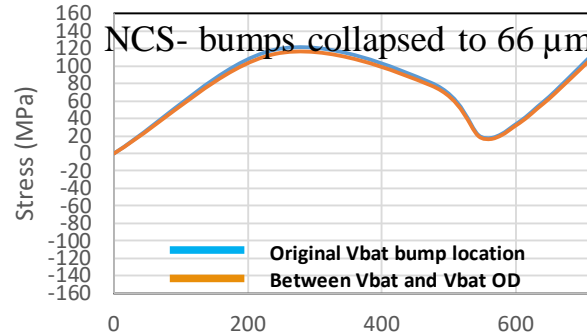
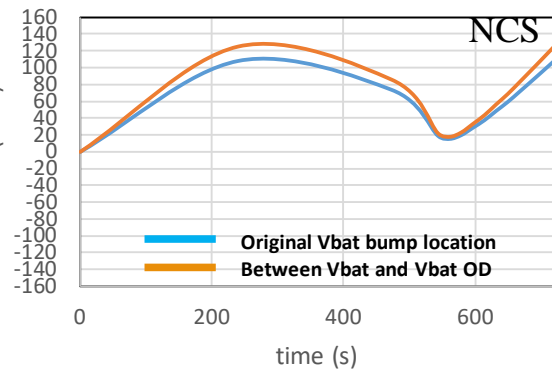
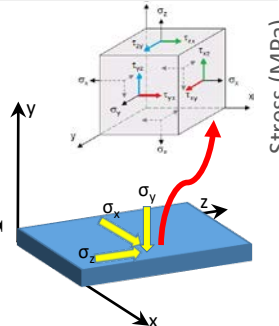


σ_y (out of plane)



$$\sigma_{\text{vbat}} = \sqrt{0.5[(\sigma_x - \sigma_y)^2 + (\sigma_y - \sigma_z)^2 + (\sigma_z - \sigma_x)^2] + 3(\sigma_{xy}^2 + \sigma_{yz}^2 + \sigma_{zx}^2)}$$

Equivalent

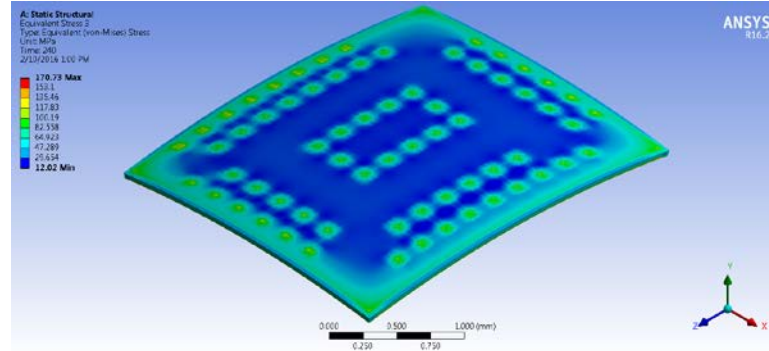
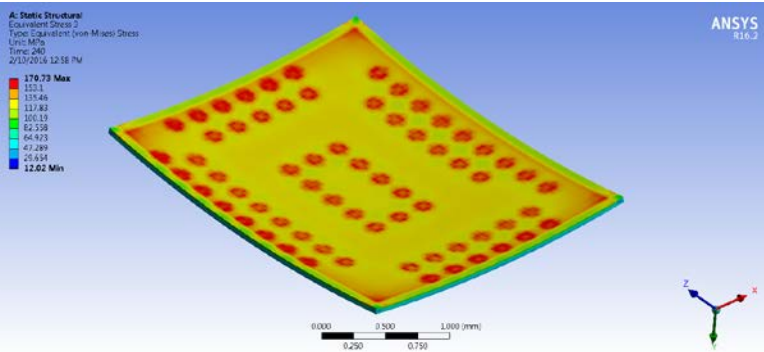


- Minimal decrease of stress when bumps are collapse 18 % of their height.
- Comparable values of equivalent stress.

The effect of thickness



Eq Stress
(MPa)



254 μm thick die

100 μm thick die

50 μm thick die

Trend with
decreasing
thickness

Stress (Mpa)

317.62

225.63

170.73

↓

Deformation (mm)

0.020537

0.049953

0.06751

↑

- Thinner dies will carry less stress, but allow more deformation (more flexible).
- The stress and strain is more localized near the bump in thinner dies.

FE analysis

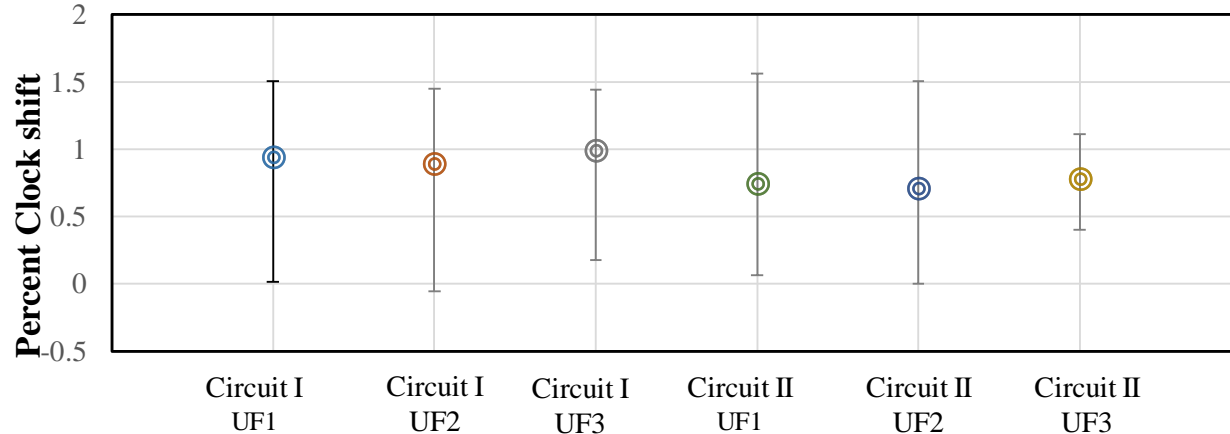
- UF reduces equivalent stress on the die! But produces a large normal-to-the-die stress.
- Relocated bump significantly reduces stress at the clock location.
- A void around Vbat and Vbat OD bumps significantly reduces the normal stresses both at Vbat location and between Vbat and Vbat OD.
- Smaller bump height has little effect on the stresses.
- Thinner dies have more flexibility and less susceptible to stress build up.



Experiments:

The effect of Underfill Material

- 3 different Ufs, tested on 2 circuits (with the same ASIC)



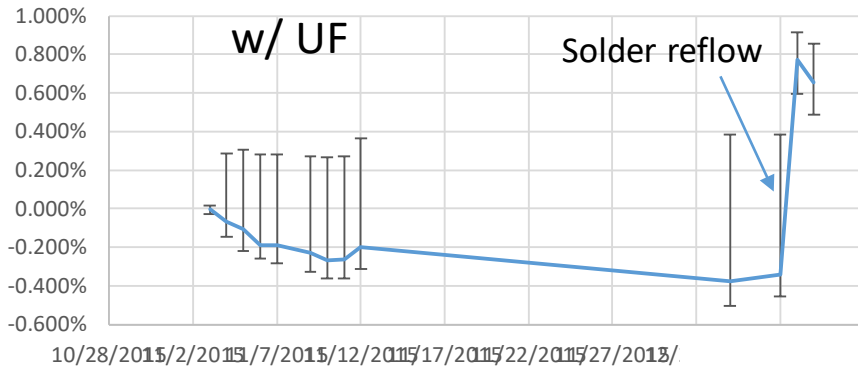
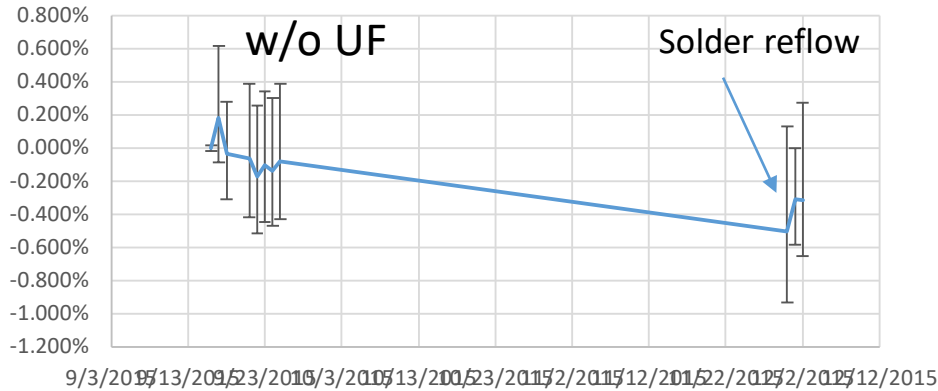
- No significant difference between different materials or different circuits.

Experiments:

Underfill/no-underfill

- Panels tested with and without UF

Clock shift vs. time

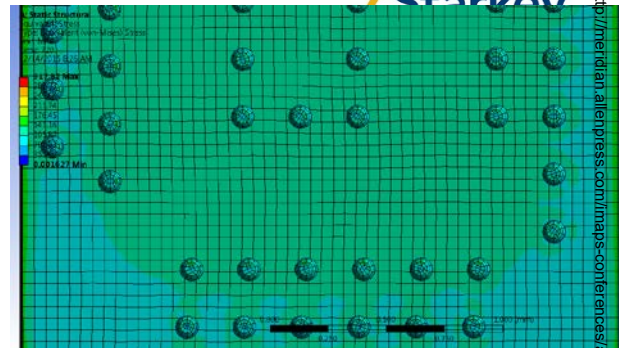


- Large thermal stresses due to CTE mismatch between Die-Solder-UF-substrate and high stiffness of UF

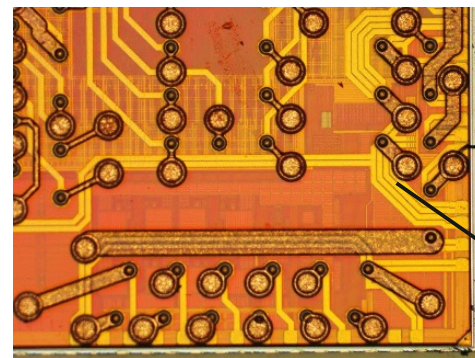
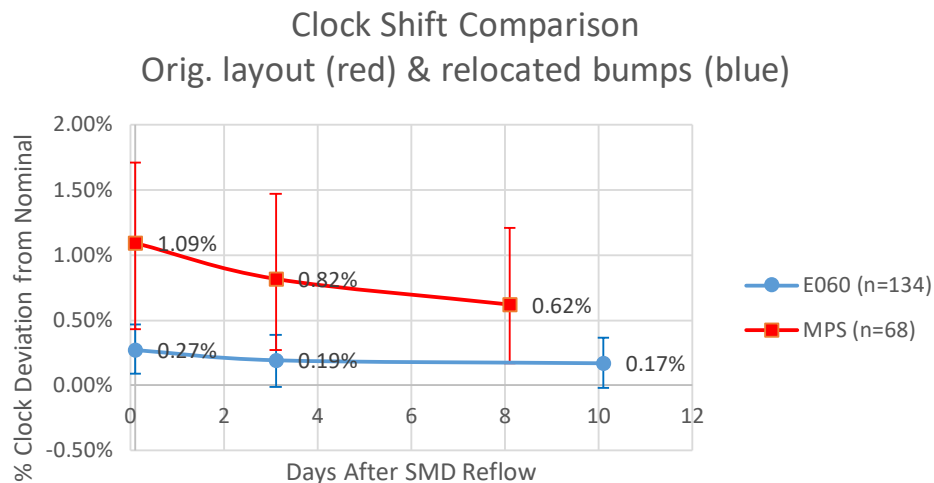


Experiments:

Effect of relocation of bumps



NP5 in Chip on Flex



NP5 relocated bumps (NP5 S-F)

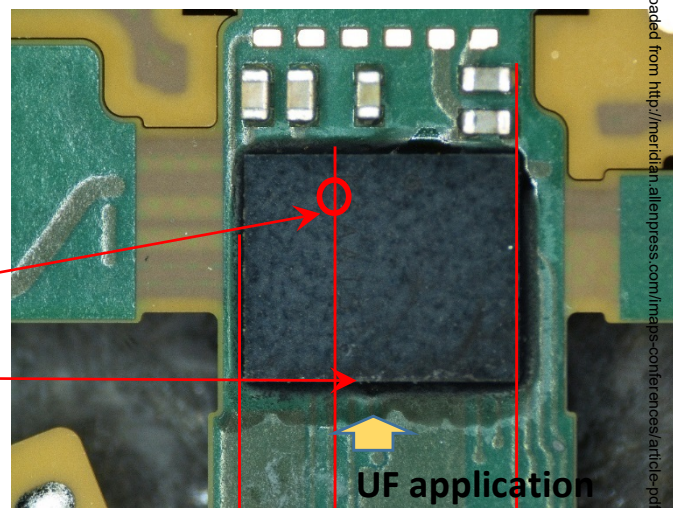
Vbat shifted
180 μm

Experiments:

Creating voids in UF

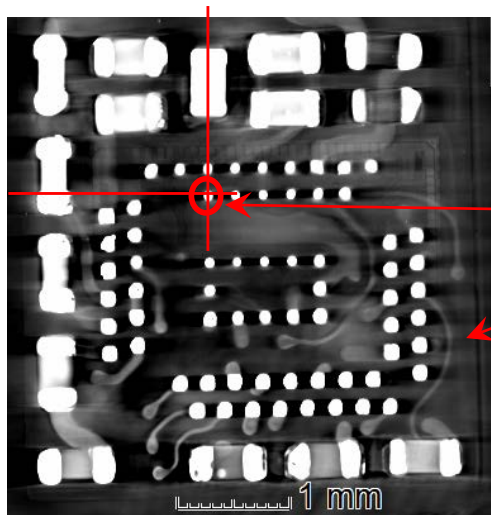
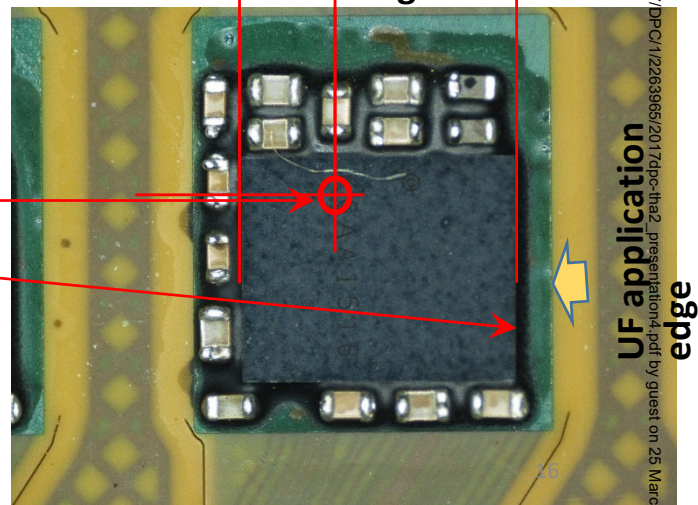
JMBN

V bat
UF application edge



NCS

V bat
UF application edge



UF application edge

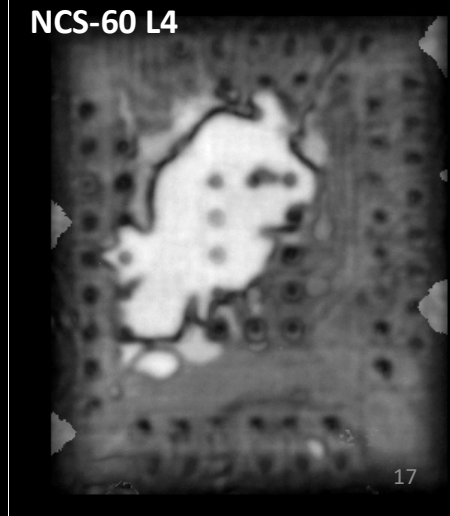
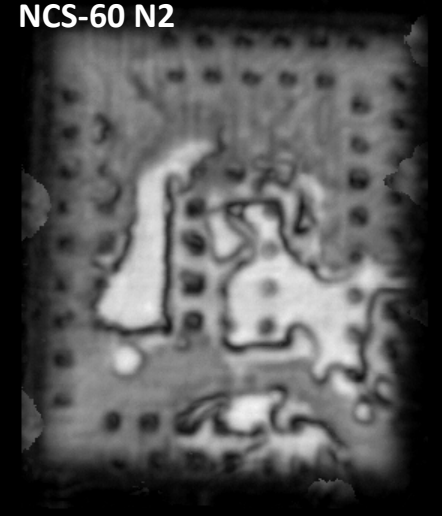
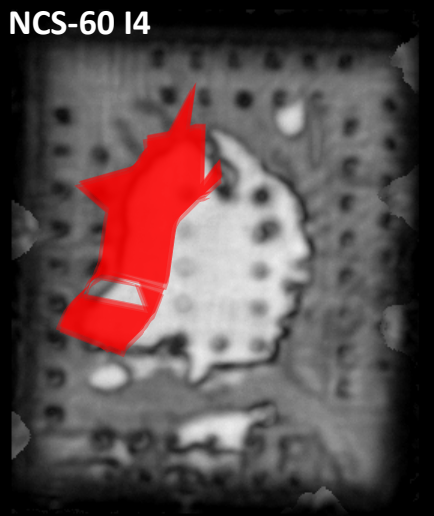
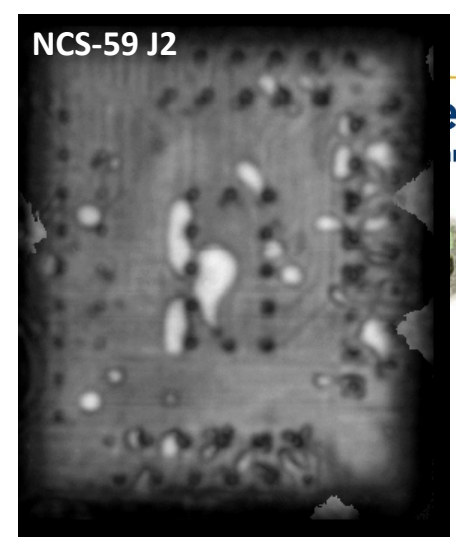
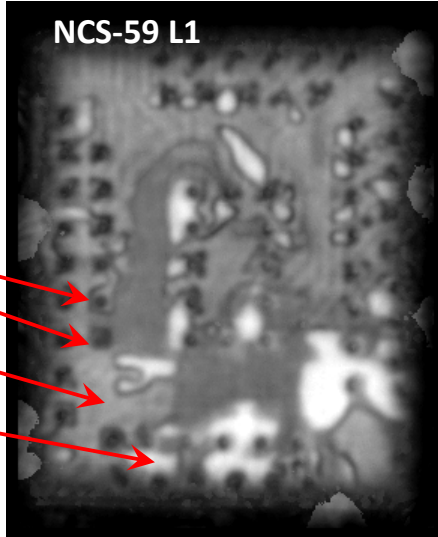
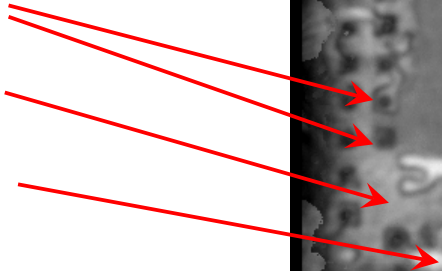
Experiments:

CSAM images

V bat & V bat OD bumps

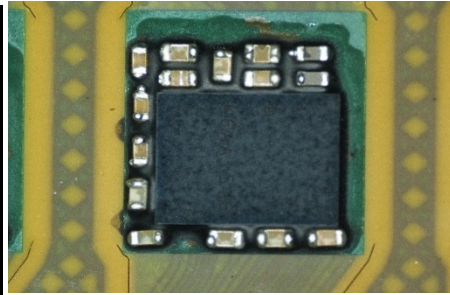
Underfill

Void/delamination



Experiments: Voids in UF vs clock shift

NCS-59 L1



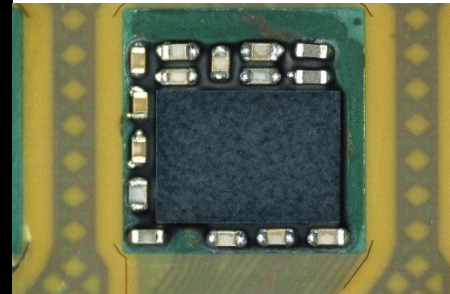
1% clock shift
during reflow

NCS-59 J2



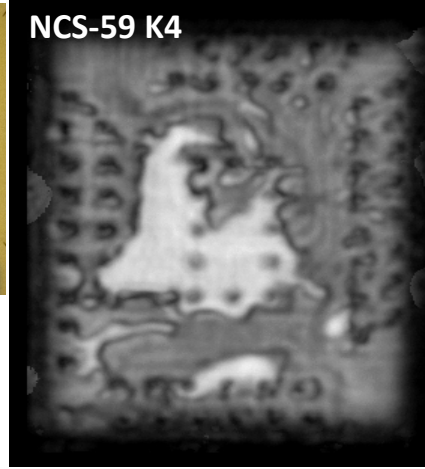
Large clock shift
+1.1% shift during
reflow

NCS-60 I4



+0.3% shift during
reflow

NCS-59 K4



Very little clock shift
-0.05% shift during
reflow

Summary

- The UF material does not improve the stress problem on the die.
 - Higher fiber content reduces CTE mismatch, however, at the same time makes UF stiffer and builds up stress with less thermal expansion.
- The normal stress is the component that affects the performance of the clock.
 - UF reduces equivalent stress on the die! But produces a large normal-to-the-die stress.
- Sometimes lower quality UF (with voids) might help with state of stress on the die.
 - A void around Vbat and Vbat OD bumps significantly reduces the normal and equivalent stresses both at Vbat location and between Vbat and Vbat OD.
- Thinner dies have more flexibility and less susceptible to stress build up. They can be a good area to explore.
- Relocated bump significantly reduces stress at the clock location.
 - An exclusion zone about the same size as the bumps pitch is recommended.



Thank you
Questions ...?

